

# Tracer Diffusivities by First-principles

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# OUTLINE

- Self-diffusion
- Exclusively first-principles
- Impurity diffusion coefficient in fcc
- Self-diffusion in hcp
- Entropy of migration
- Summary

# NO IMPURITY

- Vacancy-mediated diffusion in a cubic system

$$D_0 = f_0 c_0 w_0 a^2$$

$f_0$  – correlation factor

$a$  – lattice parameter

$c_0$  – vacancy concentration

$w_0$  – successful atom jump frequency

# SELF-DIFFUSION

$$c = \exp\left(-\frac{\Delta_f H}{k_B T}\right) \exp\left(\frac{\Delta_f S}{k_B}\right)$$

$\Delta_f H$  - enthalpy of vacancy formation

$\Delta_f S$  - vibrational entropy of vacancy formation

$$w = \tilde{\nu} \exp\left(\frac{\Delta_m S}{k_B}\right) \exp\left(-\frac{\Delta_m H}{k_B T}\right)$$

$\Delta_m H$  - enthalpy of migration

$\Delta_m S$  - vibrational entropy of migration

$\tilde{\nu}$  - characteristic vibrational frequency in the diffusion direction

# JUMP FREQUENCY

## ■ Eyring's reaction rate theory [1]

$$w = \frac{k_B T}{h} \frac{Z_{tr}^*}{Z_{in}}$$

\* represents not including the contribution of the unstable phonon mode

Partition function       $Z = \exp\left(-\frac{G}{k_B T}\right)$

$$w = \frac{k_B T}{h} \exp\left(\frac{S_{tr}^* - S_{in}}{k_B}\right) \exp\left(-\frac{(H_{tr}^* - H_{in})}{k_B T}\right)$$

NO NEED TO CALCULATE THE MIGRATION PROPERTIES

[1] Eyring, H., J. Chem. Phys. **3** (1935) 107

# FIRST-PRINCIPLES

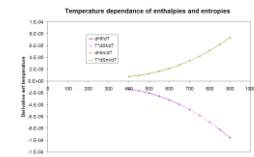
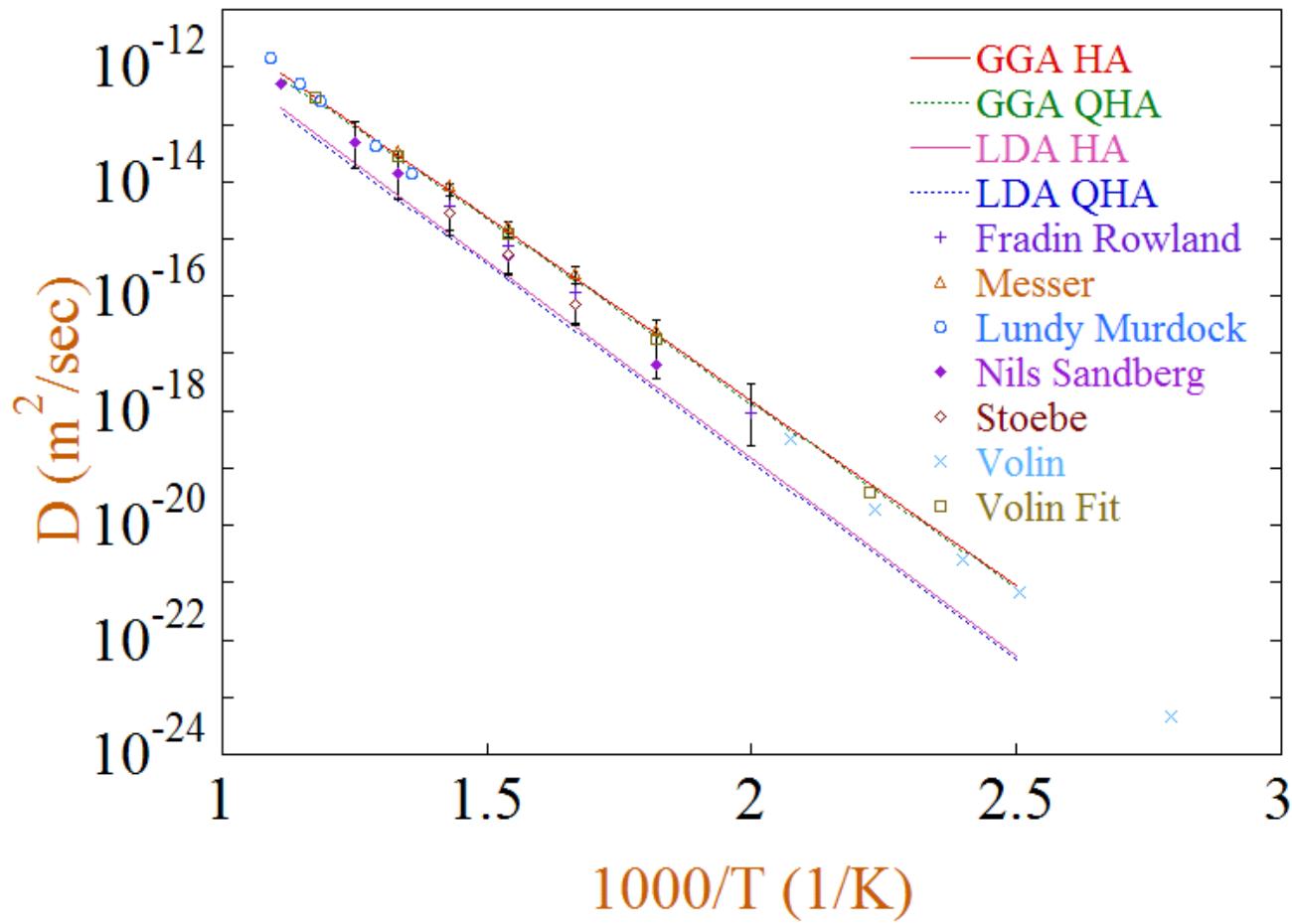
- VASP – PAW
  - System size – 32 lattice sites
- Fully relaxed perfect and equilibrium configurations
  - Volume, shape and atomic positions relaxed
- Saddle point and minimum energy saddle configuration
  - Nudged elastic band method (NEB)
- Phonon frequencies for the normal modes are determined using Supercell method (ATAT)

[Van de Walle et al, CALPHAD, 26, 539 (2002)]

# ENERGY CORRECTION

- Single vacancy in Al [Carling et al, PRL 85, 3862 (2000)]
  - Correction term: 0.15eV for GGA, 0.06eV for LDA
- Two partial vacancies in Al
  - Additional correction term: 0.05eV for GGA, 0.02eV for LDA [Sandberg, et al, PRL 89, 065901 (2002)]

# ALUMINUM SELF-DIFFUSION



- Anharmonic effects from temperature dependences are seen to be negligible.

# WITH IMPURITY

- Impurity diffusion coefficient in cubic system

$$D_2 = f_2 w_2 c_2 a^2$$

$f_2$  – impurity correlation factor

$a$  – lattice parameter

$c_2$  – vacancy concentration adjacent to impurity

$w_2$  – successful impurity jump frequency

# IMPURITY DIFFUSION

- Five-frequency model<sup>[2]</sup> best suited for diffusion in dilute fcc alloys

$$f_2 = \frac{1 + 3.5(w_3 / w_1)}{1 + (w_2 / w_1) + 3.5(w_3 / w_1)}$$

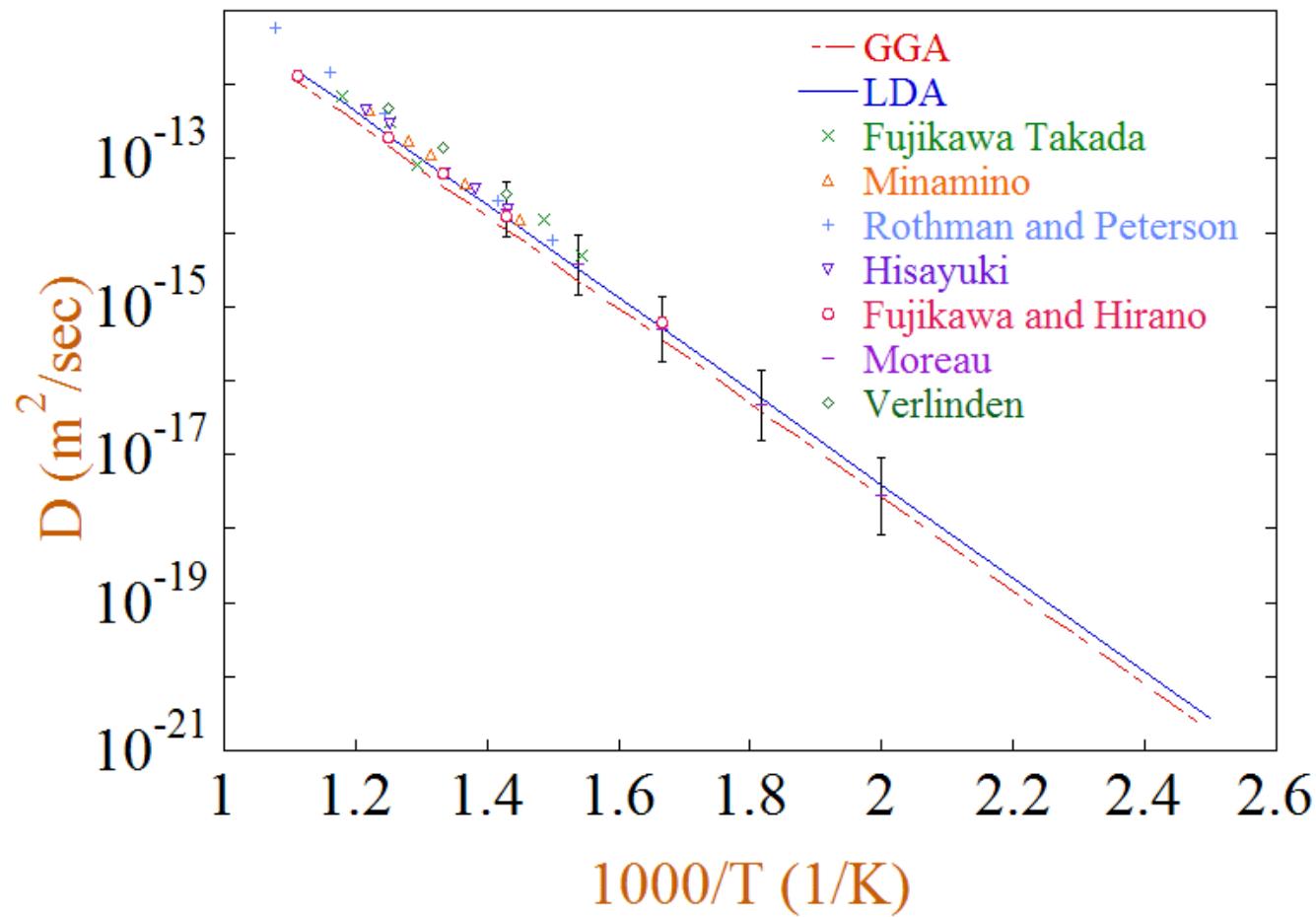
$$\frac{D_2}{D_0} = \frac{f_2}{f_0} \frac{w_2}{w_0} \frac{w_4}{w_3}$$

- Considering  $w_4$  and  $w_3$  are reverse jumps of each other we have

$$\frac{c_2}{c_0} = \exp\left(-\frac{\Delta G_b}{k_B T}\right) = \frac{w_4}{w_3}$$

[2] Le Claire, A.D., Journal of Nuclear Materials **69-70** (1978) 70

# Mg DIFFUSIVITY IN Al



- No correction term - different jumps need different corrections

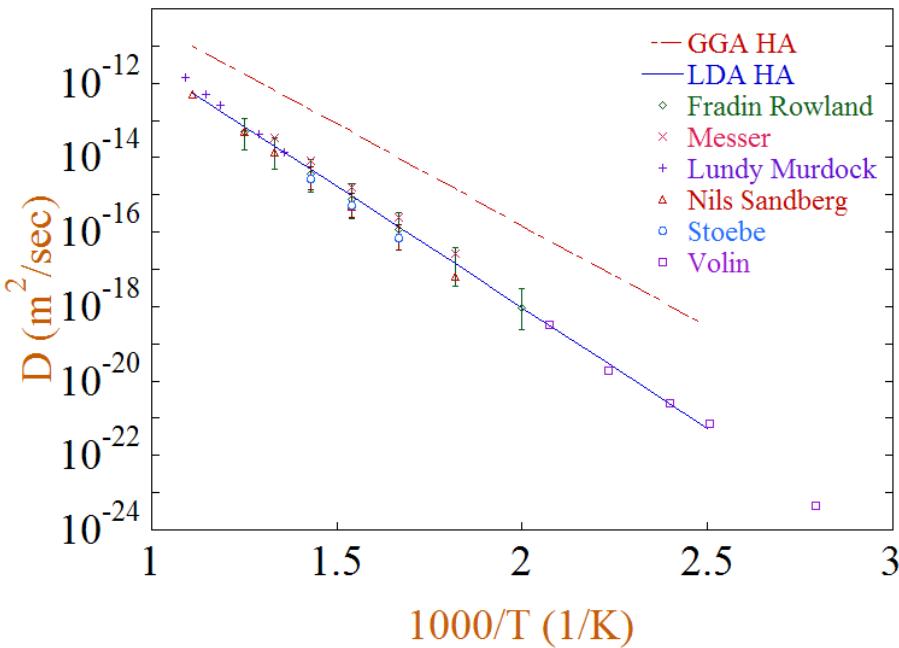
## PAW LDA – NO CORRECTION

- LDA - cancellation of errors between the exchange and correlation energies [4] making it more suitable for surface calculations.
- Energy calculation of the surface due to vacancy from LDA is reasonable.
- In diffusion calculation - errors due to over-binding from LDA get canceled.

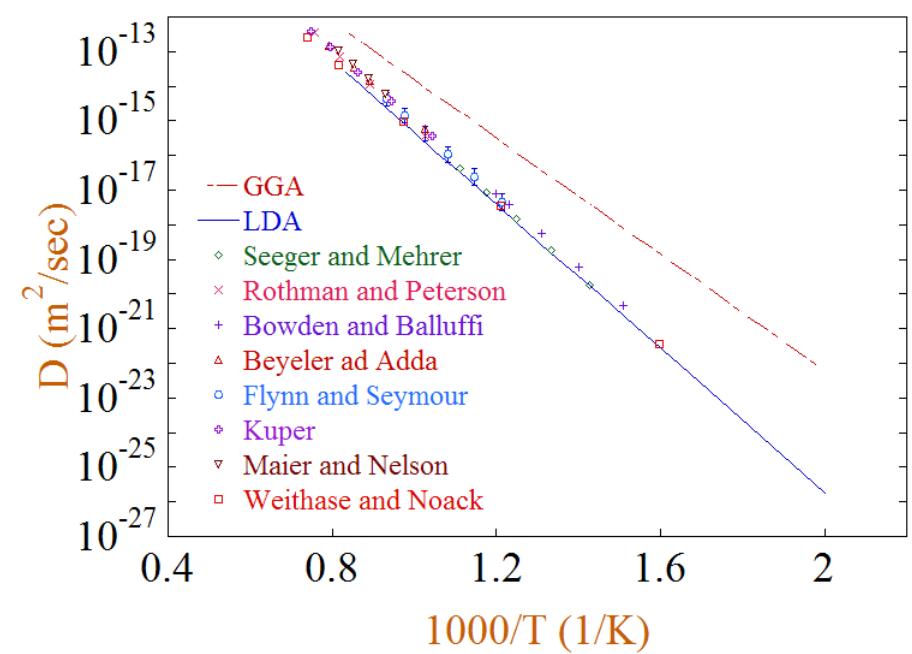
[4] Vitos, L., Surface Science **411** (1998) 186

# SELF-DIFFUSION RESULTS

## ALUMINUM SELF-DIFFUSION



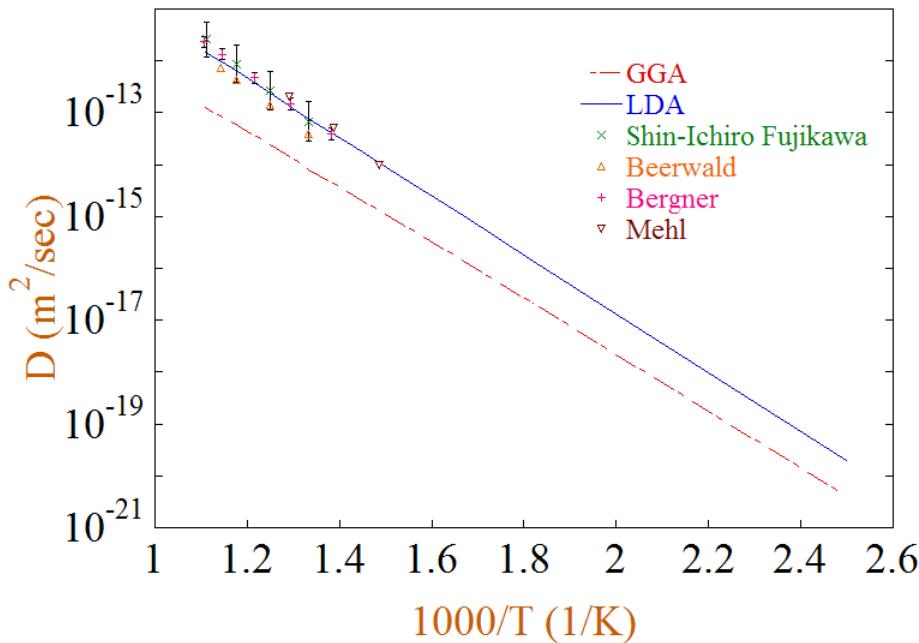
## COPPER SELF-DIFFUSION



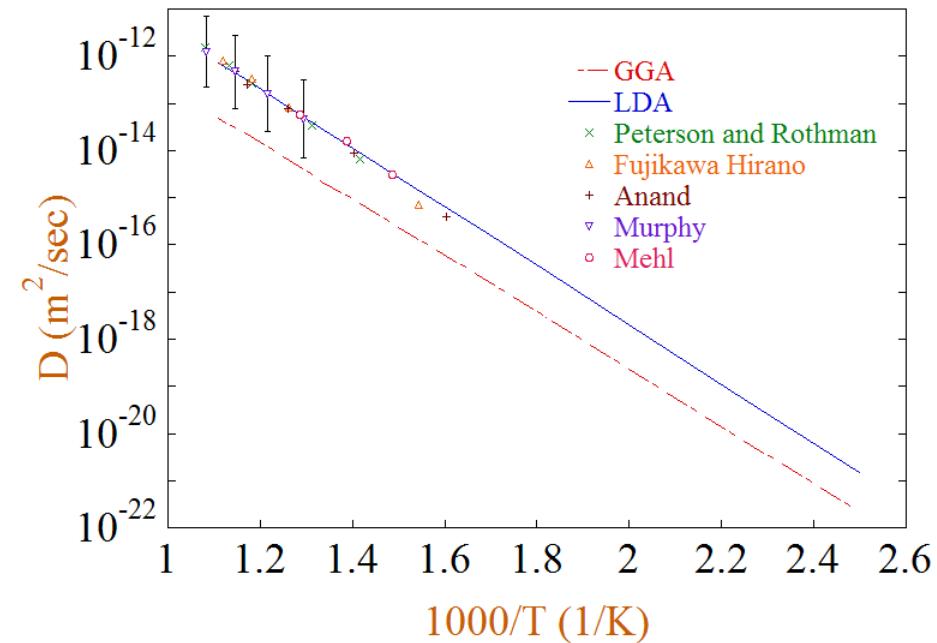
NO CORRECTION

# IMPURITY DIFFUSION RESULTS

Si DIFFUSIVITY IN Al

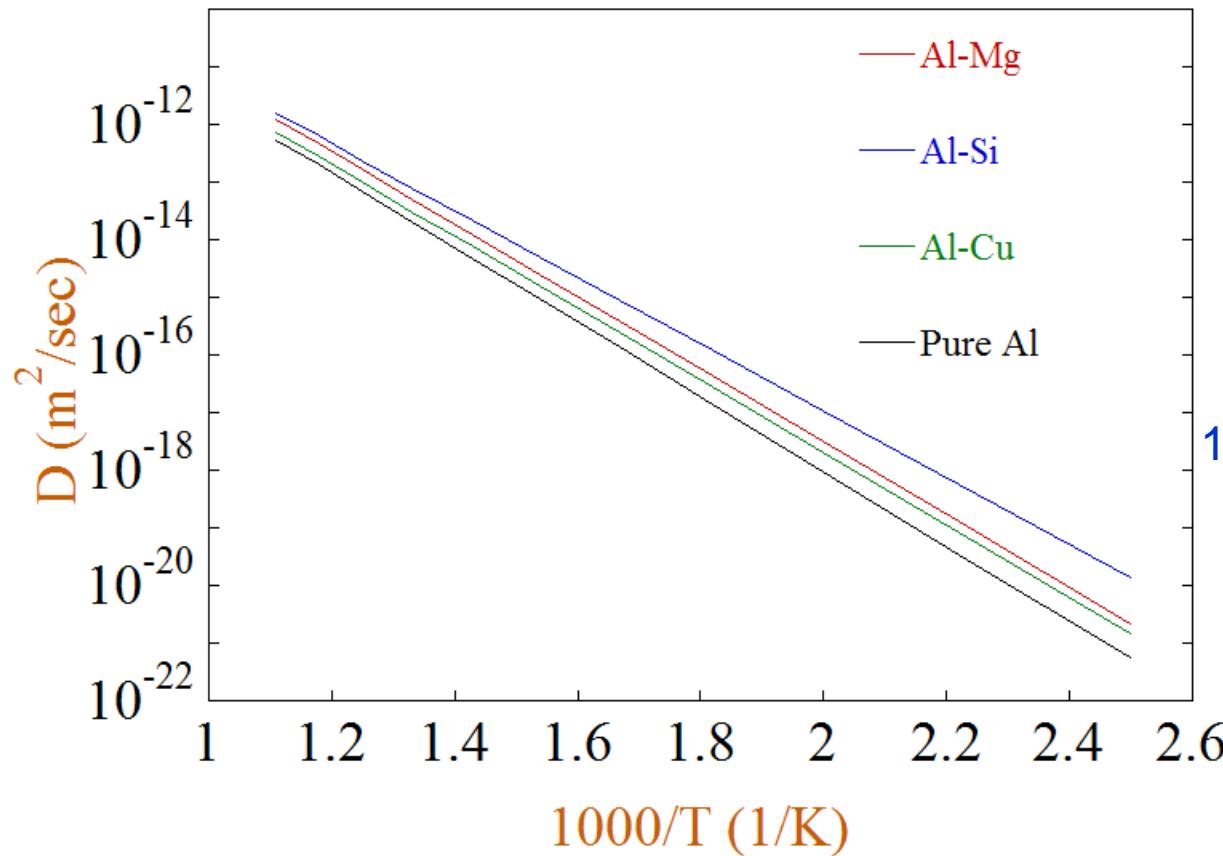


Cu DIFFUSIVITY IN Al



NO CORRECTION

# OBSERVATION



$r_{\text{Mg}} > r_{\text{Al}} > r_{\text{Si}} > r_{\text{Cu}}$  [5]

$1.597 > 1.431 > 1.392 > 1.284$

- Impurity diffusivities do not follow the trend of their size

[5] Y. Wang et.al., CALPHAD, 28 (2004) 79-90

# SELF-DIFFUSION IN HCP

## ■ Diffusion in hexagonal cubic system

$$D_x = \frac{1}{2} Ca^2 (3w_A f_{Ax} + w_B f_{Bx})$$

$$D_z = \frac{3}{4} Cc^2 w_B f_{Bz}$$

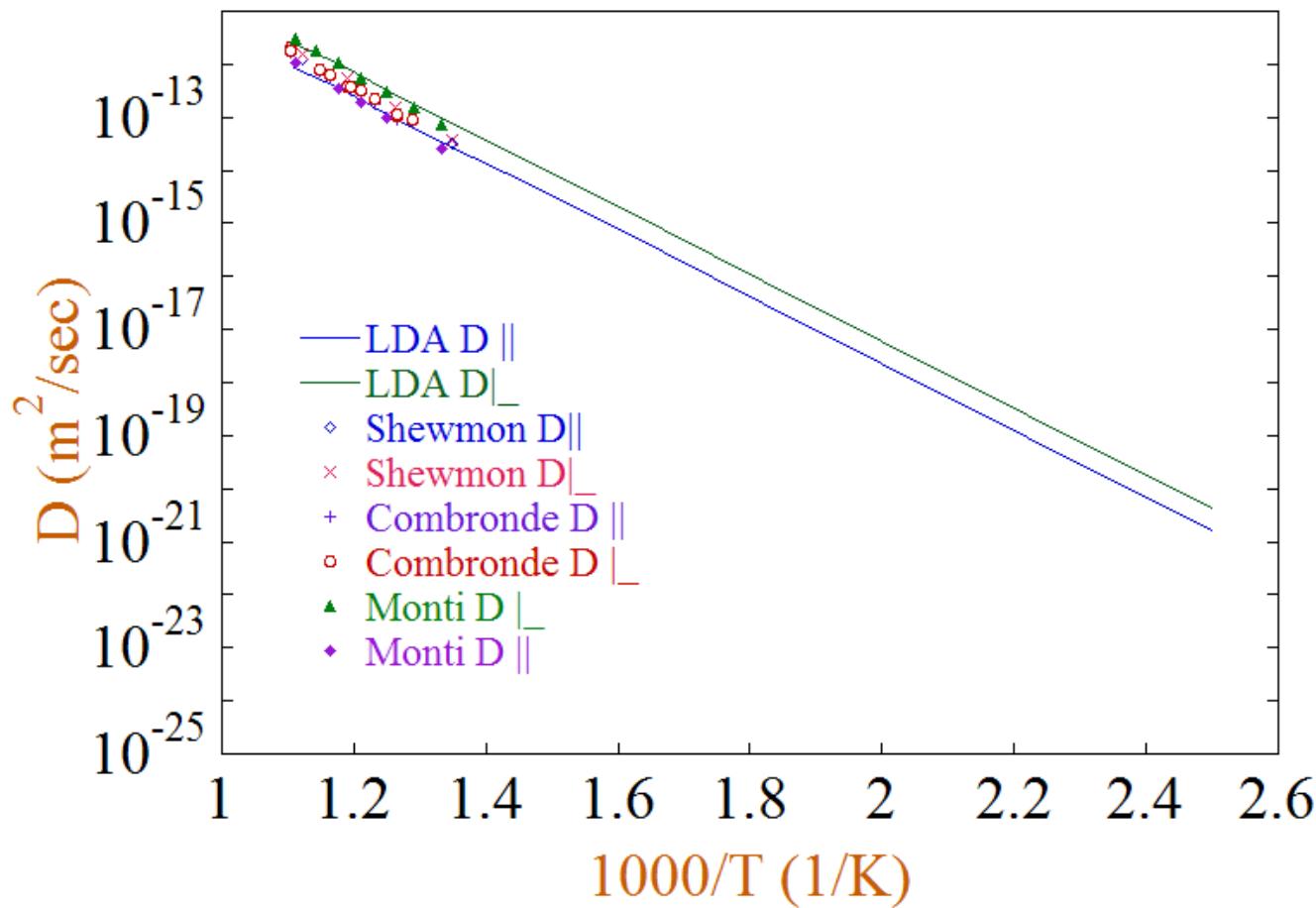
$f_{ij}$  – correlation factors function of  $w_A / w_B$  ratio

$a, c$  – lattice parameters along x,z axes

$C$  – vacancy concentration

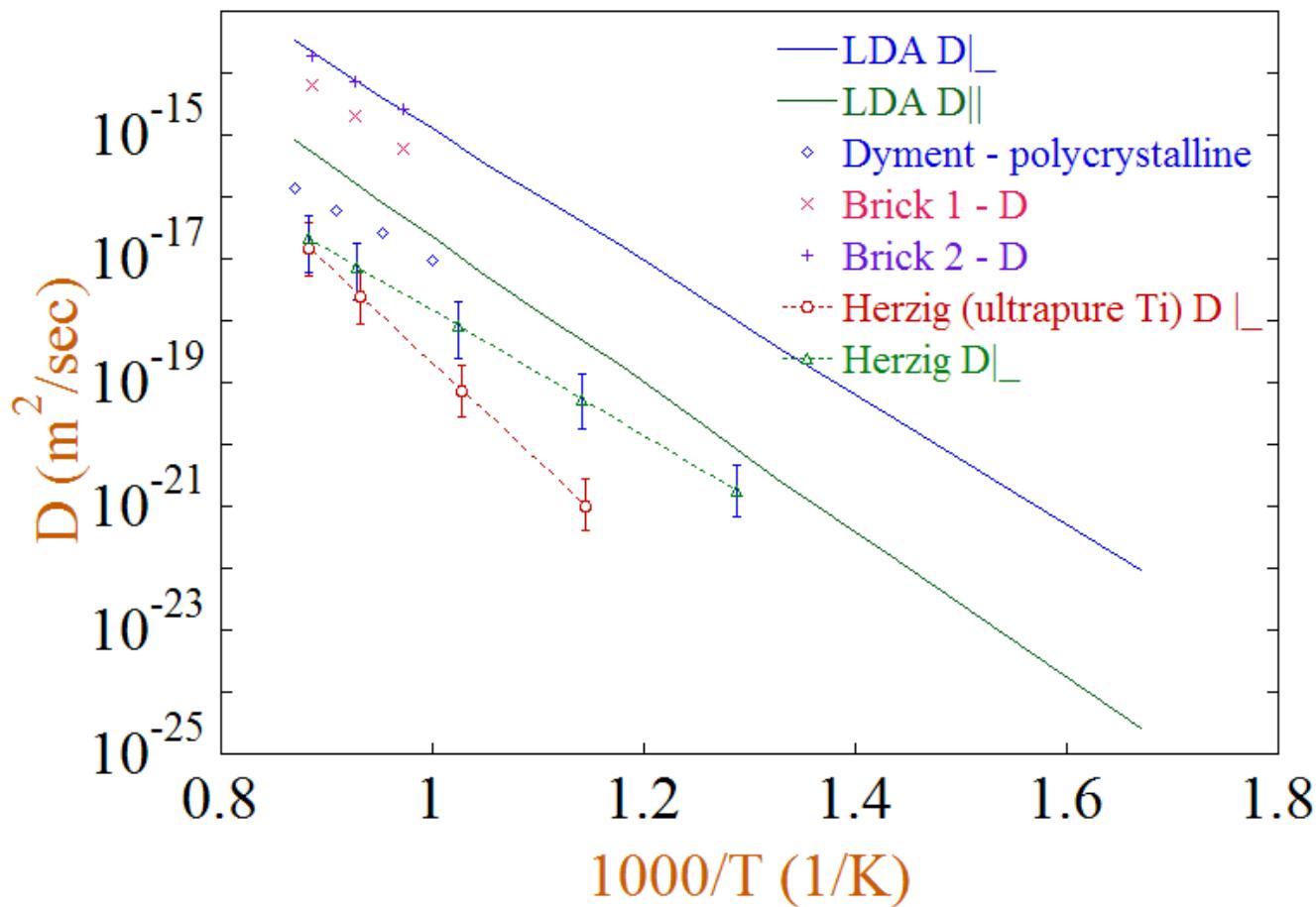
$w_A, w_B$  – successful jump frequency |\_ and || to z-axis

# MAGNESIUM SELF-DIFFUSION



- Diffusion in the basal plane higher than along z-axis

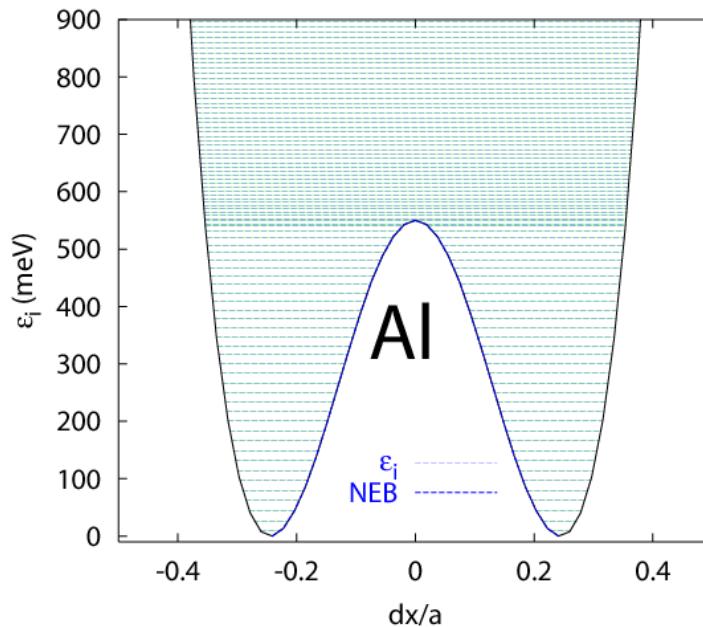
# TITANIUM SELF-DIFFUSION



- High difference in diffusivities between  $\parallel$  &  $\perp$  directions

# ENTROPY OF MIGRATION

- Entropy of migration is defined as  $\Delta S_m = S_{tr} - S_{in}$
- We need to calculate entropy contribution  $\tilde{S}$  from the unstable mode.



$$\tilde{Z} = \sum_i \exp\left(\frac{-\epsilon_i}{k_B T}\right)$$

$$\tilde{v} = \frac{k_B T}{h \tilde{Z}}$$

# SUMMARY

- General procedure to calculate atom jump frequencies from static first-principles is presented.
- Accurate tracer diffusivities can be obtained exclusively from first-principles with LDA.
- Anharmonic effects due to temperature dependences of the quantities is minimum – curvature in D mostly due to di-vacancies at high T.
- Solute diffusivities do not follow the trend of their size.
- In hcp, self-diffusion in the basal plane seen to be higher than in normal.
- Calculated entropy of migration and characteristic vibrational frequency.

THANK YOU FOR LISTENING



# EQUATIONS

$$F = E^* + Nk_B T \int_0^\infty \ln \left[ 2 \sinh \left( \frac{h\nu}{2k_B T} \right) \right] g(\nu) d\nu$$

Simplified high temperature ( $T > \theta_D$ ) form

$$S = k_B \int_0^\infty \left[ \left( \frac{h\nu}{2k_B T} \right) \coth \left( \frac{h\nu}{2k_B T} \right) - \ln \left[ 2 \sinh \left( \frac{h\nu}{2k_B T} \right) \right] \right] g(\nu) d\nu$$

$$U = E^* + 0.5 \int_0^\infty h\nu \coth \left( \frac{h\nu}{2k_B T} \right) g(\nu) d\nu$$

$$\begin{aligned} F &= E^* + Nk_B T \int_0^\infty \ln \left( \frac{h\nu}{k_B T} \right) g(\nu) d\nu \\ &= E^* + k_B T \sum_m \ln \left( \frac{h\nu_i}{k_B T} \right) \end{aligned}$$

$m$  – vibrational degrees of freedom

$E^*$  is the 0K energy of the system in equilibrium

$\nu$  represents the phonon frequencies of the system

$g(\nu)$  represents the phonon DOS

$$U_{vib} = F_{vib} + TS$$

where

$$F_{vib} = k_B T \sum_m \ln \left( \frac{h\nu_i}{k_B T} \right)$$

$$U_{vib} = k_B T \left( \sum_m \ln \left( \frac{\left( \frac{h\nu_i}{k_B T} \right)}{\left( \frac{h\nu_i}{ek_B T} \right)} \right) \right) = mk_B T \quad \Rightarrow \tilde{U} = k_B T$$

# HARMONIC THEORY

- Equations defining enthalpy and entropy

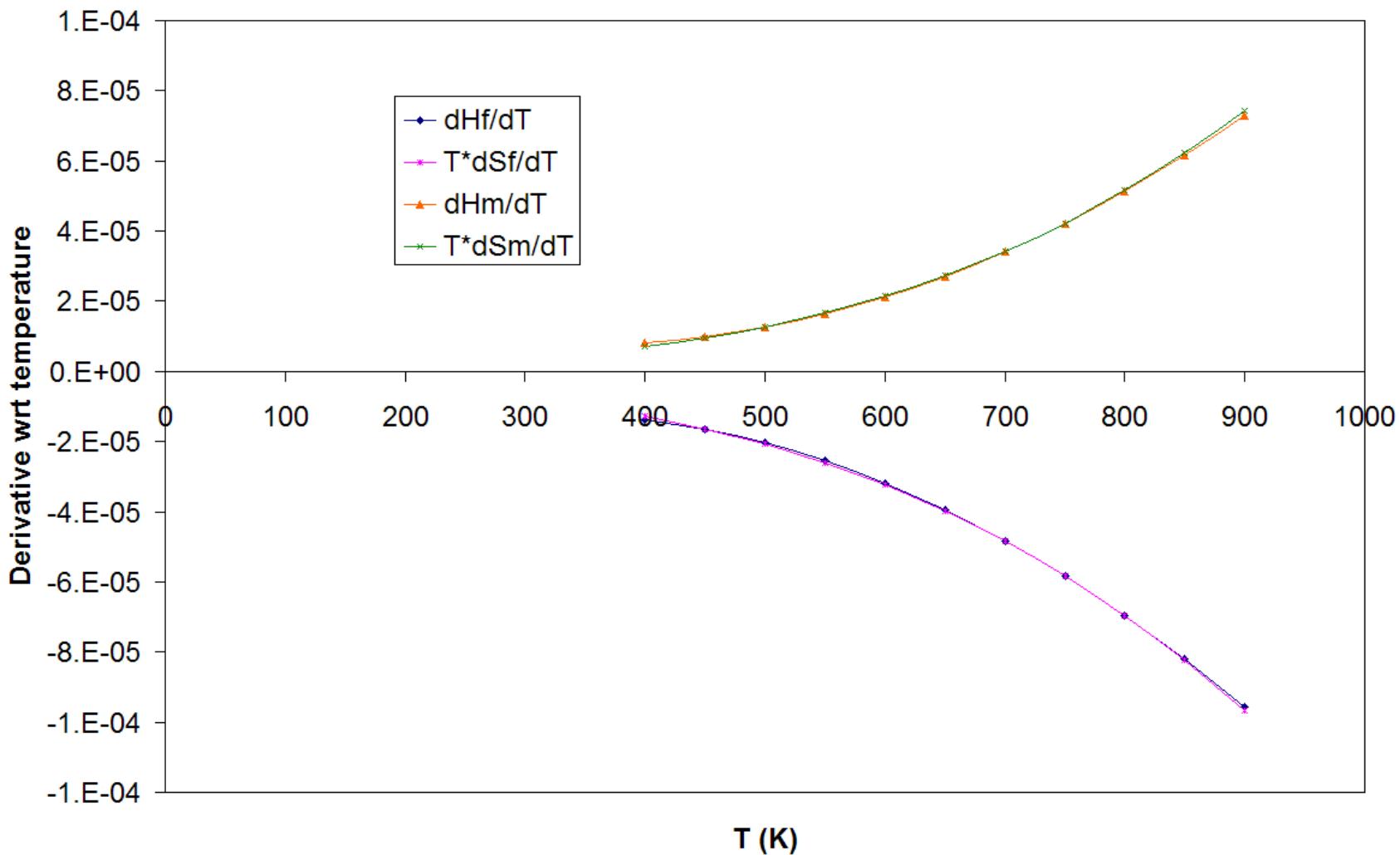
$$F(V, T) = E(V) + k_B T \sum_j \ln \left[ 2 \sinh \left( \frac{h v_j(V)}{2k_B T} \right) \right]$$

$$S(V, T) = k_B \sum_j \left[ \left( \frac{h v_j(V)}{2k_B T} \right) \coth \left( \frac{h v_j(V)}{2k_B T} \right) - \ln \left[ 2 \sinh \left( \frac{h v_j(V)}{2k_B T} \right) \right] \right]$$

$$H(V, T) = F(V, T) + TS(V)$$

where the summation  $j$  is over all the vibrational degrees of freedom (DOF)

## Temperature dependance of enthalpies and entropies



# IMPURITY DIFFUSION RESULTS

System	$\Delta H_f$ (eV)	$\Delta S_f$ (k <sub>B</sub> )	$\Delta H_m$ (eV)	$\Delta S_m$ (k <sub>B</sub> )	$\tilde{\nu}$ (THz)	w (MHz)	f	$D_0$ (m <sup>2</sup> /s)	Q (eV)
Pure Al	0.706	1.20	0.58	2.28	2.26	1.08	0.78	8e-6	1.286
Al-Mg	0.743	1.57	0.42	2.74	1.54	66.6	0.17	1e-5	1.246
Al-Si	0.627	1.03	0.55	2.59	1.41	1.24	0.67	4e-6	1.154
Al-Cu	0.692	0.49	0.56	1.90	0.94	0.25	0.99	7e-6	1.239

- where  $\tilde{\nu}$  is the frequency of vibration in the direction of diffusion, w is the successful jump frequency, f is the correlation factor.
- The quantities pertain to the diffusion of Al in the case of pure Al and diffusion of the impurity in the case of impurity-containing systems.
- The values listed are for T=400K

# PHYSICAL INTERPRETATION

- Migration barrier is smaller for larger impurity
  - Difference in strain at the initial and transition states is small for a large impurity [3]
- Activation barrier in the case of impurity diffusion also includes the term  $d \ln f_2 / dT$  ( $Q \neq \Delta H_f + \Delta H_m$ )

System	$Q$ (eV)	$\Delta H_f + \Delta H_m$	$d \ln f_2 / dT$	$D_0$ (m <sup>2</sup> /s)
Pure Al	1.285	1.286	0	8e-6
Al-Mg	1.246	1.165	0.081	1e-5
Al-Si	1.154	1.178	-0.024	4e-6
Al-Cu	1.239	1.252	-0.013	7e-6

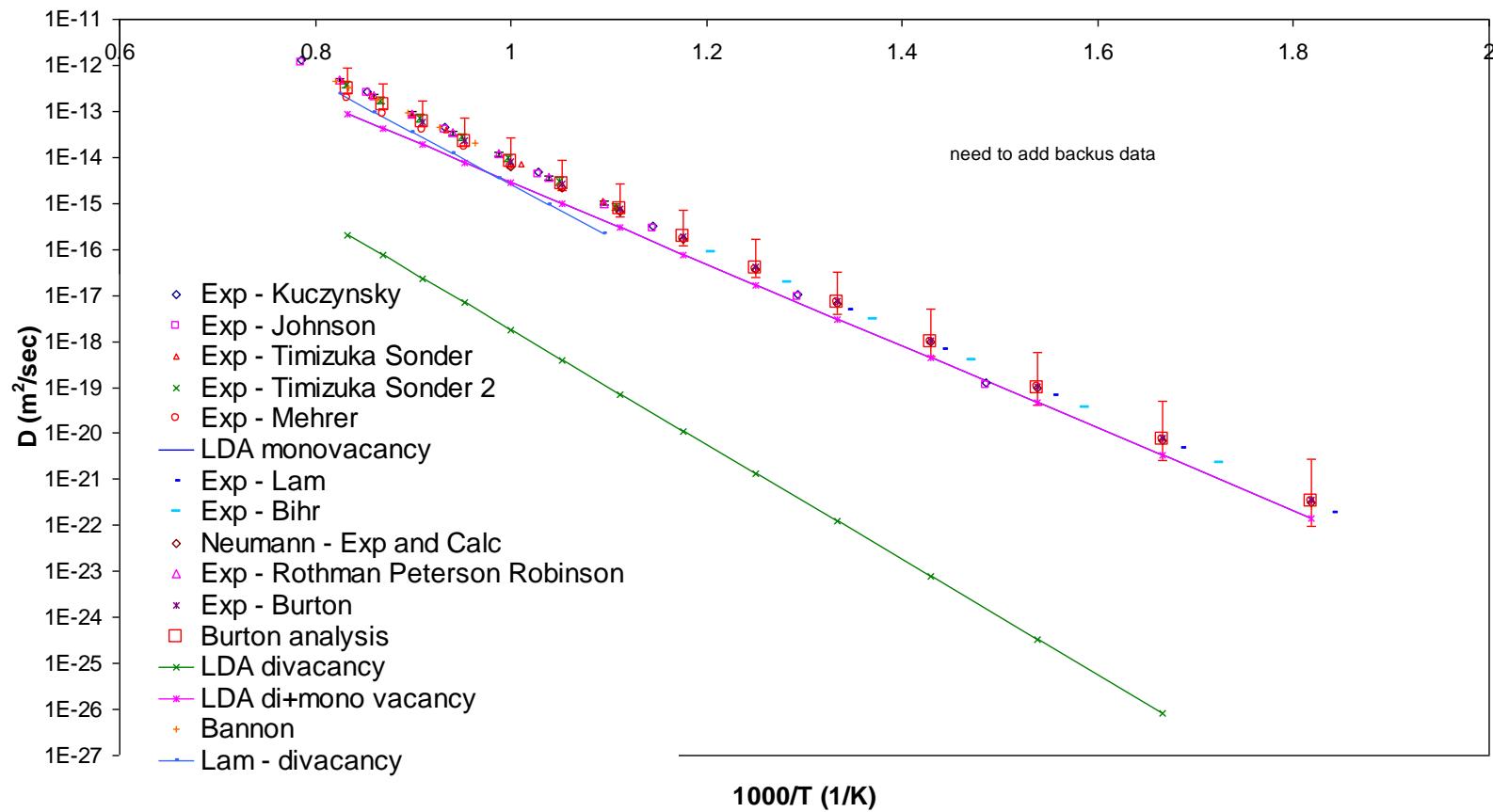
- From  $D_0$  and  $Q$  values, we obtain  $D_{\text{Al-Si}} > D_{\text{Al-Mg}} > D_{\text{Al-Cu}}$

## PHYSICAL INTERPRETATION

- Interpretation of trends of the quantities involved in  $D_0$  and Q for different diffusing species can be explained based on
  - Valency
  - Unscreened nuclear charge
  - Mass
  - Size

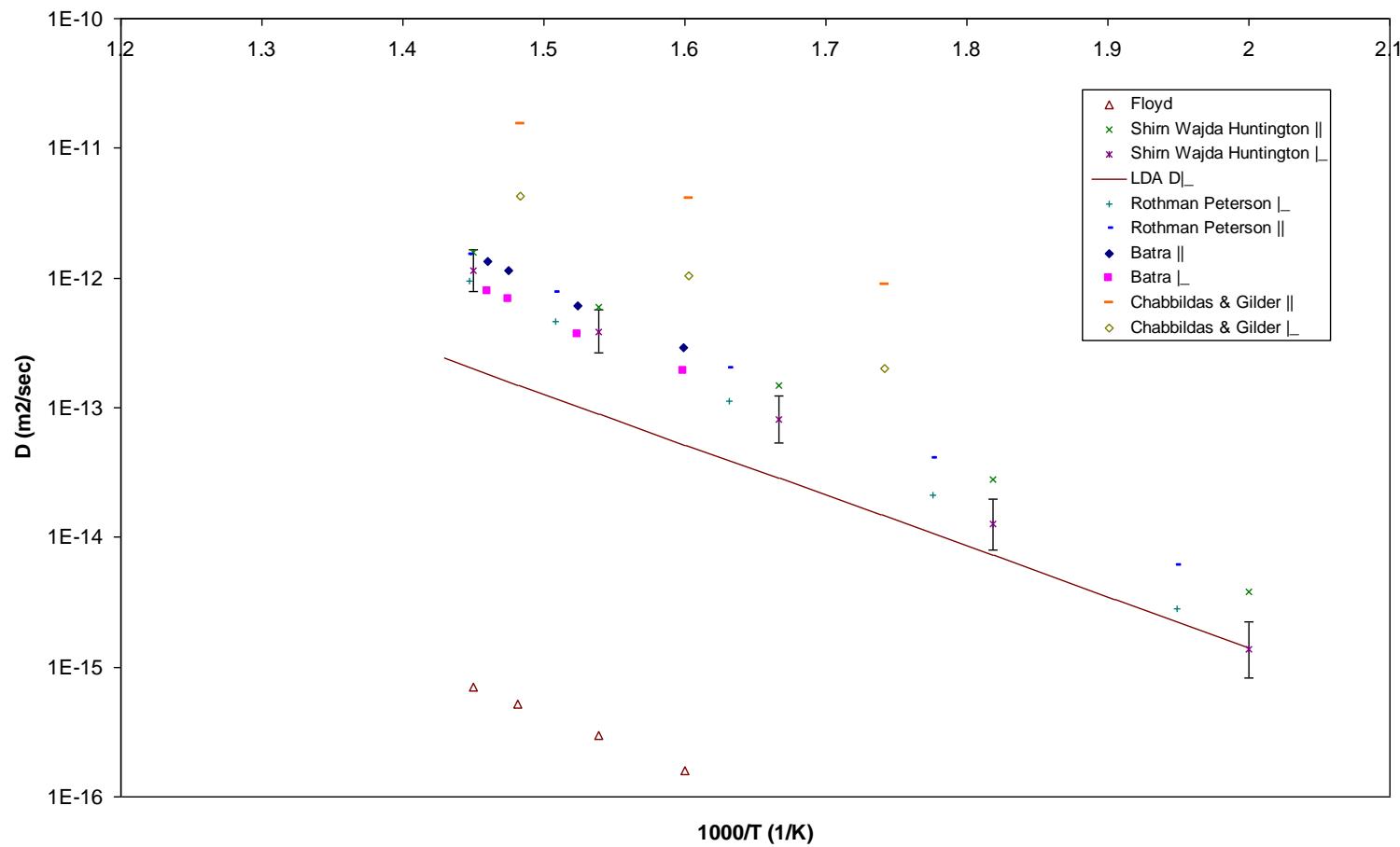
# Ag di-vacancy

## Ag self-diffusion (LDA - no correction term)

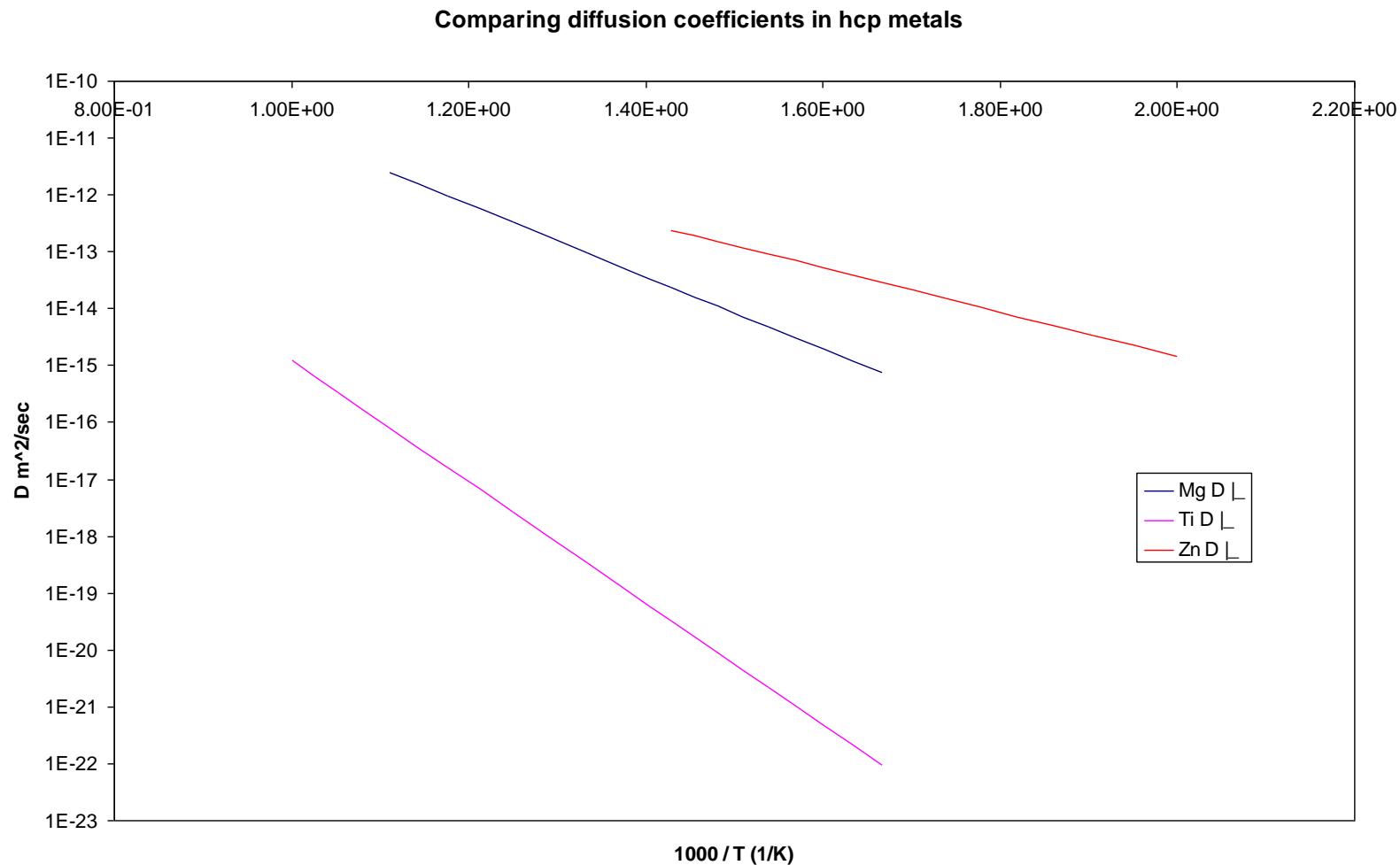


# Zn hcp

Zn self-diffusion

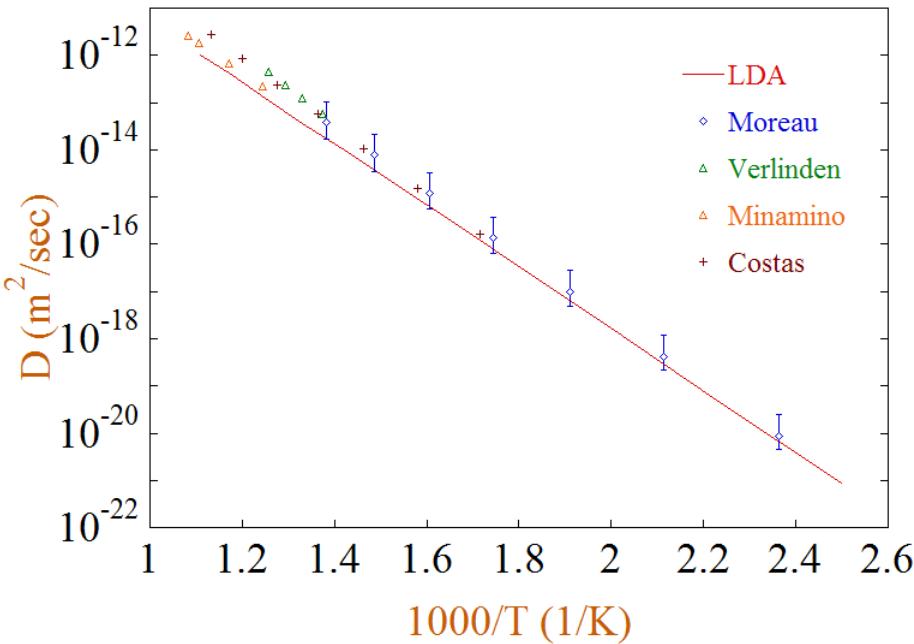


# HCP self-diffusion

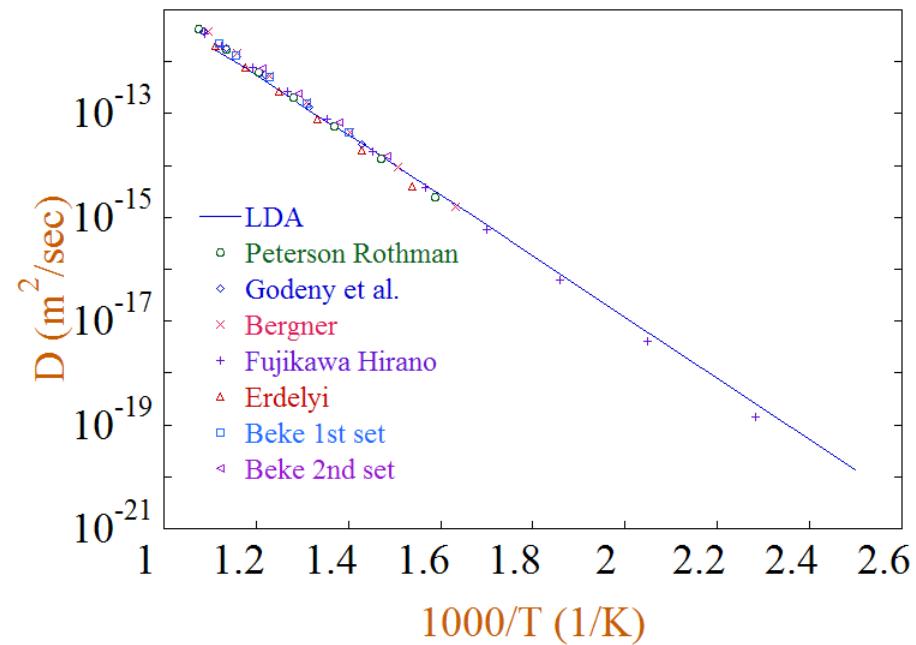


# IMPURITY DIFFUSION RESULTS

Li DIFFUSIVITY IN Al



Zn DIFFUSIVITY IN Al



NO CORRECTION